Figure 1

Figure 2

Figure 3a

Figure 3b

Figure 4

Figure 5

Figure 6a

Figure 6b

Figure 7

Figure 8

Figure 9

start

Provide a generation beam — 800

Provide an analyzer beam — 810

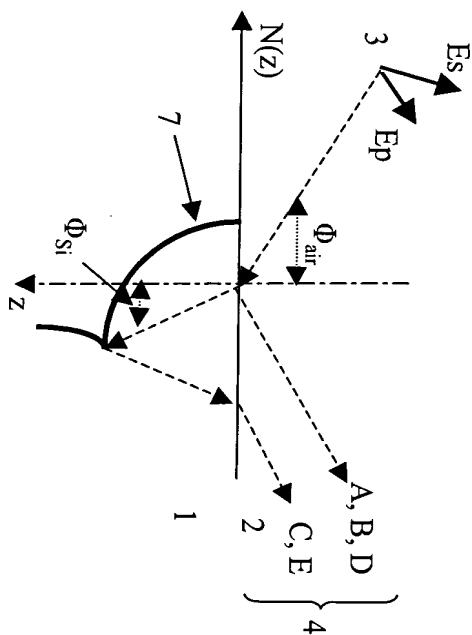Focus the generation beam and the analyzer beam — 820

Generate a number of excess charge carriers — 830

Reflect the analyzer beam — 840

Detect a predetermined characteristic of the reflected analyzer beam — 850

Eliminate at least the near surface contribution — 860

Determine the value of a bulk property — 870

end

Figure 10

start

Focus the generation beam and the probe beam — 900

Generate a number of excess charge carriers — 910

Reflect the probe beam — 920

Detect a predetermined characteristic of the reflected probe beam — 930

Remove at least the near surface contribution — 940

Evaluate the semiconductor substrate based on a remaining contribution — 950

end

Figure 11

start

Create a plurality of excess carriers — 1110

Focus a probe beam — 1120

Reflect the probe beam — 1130

Detect a predetermined characteristic of the reflected probe beam — 1140

Remove at least the near surface contribution — 1150

Evaluate the semiconductor substrate based on a remaining contribution — 1160

end